FAIRCHILD SEMICONDUCTOR™

GlobalOptoisolator™

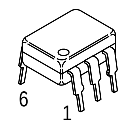
VDE	UL	CSA	SETI	SEMKO	DEMKO	NEMKO	BABT

MOC8100

6-Pin DIP Optoisolator Transistor Output

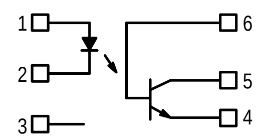
The MOC8100 device consists of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector. It is designed for applications requiring higher output collector current (I_C) with lower input drive current (I_F).

- Current Transfer Ratio Guaranteed to be > 50% at 1 mA LED Drive Level
- ***To order devices that are tested and marked per VDE 0884 requirements, the suffix ”V” must be included at end of part number. VDE 0884 is a test option.***



STANDARD THRU HOLE

SCHEMATIC



PIN 1. LED ANODE
2. LED CATHODE
3. N.C.
4. EMITTER
5. COLLECTOR
6. BASE

Applications

- Appliances, Measuring Instruments
- General Purpose Switching Circuits
- Programmable Controllers
- Portable Electronics
- Interfacing and coupling systems of different potentials and impedances
- Low Power Logic Circuits
- Telecommunications Equipment

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
INPUT LED			
Reverse Voltage	V_R	6	Volts
Forward Current — Continuous	I_F	60	mA
LED Power Dissipation @ T_A = 25°C with Negligible Power in Output Detector Derate above 25°C	P_D	120 1.41	mW mW/°C
OUTPUT TRANSISTOR			
Collector–Emitter Voltage	V_{CEO}	30	Volts
Emitter–Base Voltage	V_{EBO}	7	Volts
Collector–Base Voltage	V_{CBO}	70	Volts
Collector Current — Continuous	I_C	150	mA
Detector Power Dissipation @ T_A = 25°C with Negligible Power in Input LED Derate above 25°C	P_D	150 1.76	mW mW/°C
TOTAL DEVICE			
Isolation Surge Voltage(1) (Peak ac Voltage, 60 Hz, 1 sec Duration)	V_{ISO}	7500	Vac(pk)
Total Device Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	250 2.94	mW mW/°C
Ambient Operating Temperature Rang	T_A	–55 to +100	°C
Storage Temperature Range	T_{stg}	–55 to +150	°C
Soldering Temperature (10 sec, 1/16″ from case)	T_L	260	°C

1. Isolation surge voltage is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)(1)

Characteristic		Symbol	Min	Typ(1)	Max	Unit
INPUT LED						
Forward Voltage (I_F = 10 mA)	T_A = 0–70°C T_A = –55°C T_A = 100°C	V_F	— — —	1.15 1.3 1.05	1.4 — —	Volts
Reverse Leakage Current (V_R = 6 V)		I_R	—	0.05	10	µA
Capacitance (V = 0 V, f = 1 MHz)		C_J	—	18	—	pF
OUTPUT TRANSISTOR						
Collector–Emitter Dark Current	(V_{CE} = 5 V, T_A = 25°C)	I_{CEO}	—	3	25	nA
	(V_{CB} = 30 V, T_A = 70°C)	I_{CEO}	—	0.05	50	µA
Collector–Base Dark Current (V_{CB} = 5 V)		I_{CBO}	—	0.2	10	nA
Collector–Emitter Breakdown Voltage (I_C = 1 mA)		$V_{(BR)CEO}$	30	45	—	Volts
Collector–Base Breakdown Voltage (I_C = 100 µA)		$V_{(BR)CBO}$	70	100	—	Volts
Emitter–Base Breakdown Voltage (I_E = 100 µA)		$V_{(BR)EBO}$	7	7.8	—	Volts
DC Current Gain (I_C = 1 mA, V_{CE} = 5 V) (Typical Value)		h_{FE}	—	600	—	—
Collector–Emitter Capacitance (f = 1 MHz, V_{CE} = 0)		C_{CE}	—	7	—	pF
Collector–Base Capacitance (f = 1 MHz, V_{CB} = 0)		C_{CB}	—	19	—	pF
Emitter–Base Capacitance (f = 1 MHz, V_{EB} = 0)		C_{EB}	—	9	—	pF
COUPLED						
Output Collector Current (I_F = 1 mA, V_{CE} = 5 V) (I_F = 1 mA, V_{CE} = 5 V, T_A = 0 to +70°C)		I_C (CTR)(2)	 0.5 (50) 0.3 (30)	 1 (100) 0.6 (60)	 — —	mA (%)
Collector–Emitter Saturation Voltage (I_C = 100 µA, I_F = 1 mA)		$V_{CE(sat)}$	—	0.22	0.5	Volts
Turn–On Time (I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω)(3)		t_{on}	—	9	20	µs
Turn–Off Time (I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω)(3)		t_{off}	—	7	20	µs
Rise Time (I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω)(3)		t_r	—	3.8	—	µs
Fall Time (I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω)(3)		t_f	—	5.6	—	µs
Isolation Voltage (f = 60 Hz, t = 1 sec)(4)		V_{ISO}	7500	—	—	Vac(pk)
Isolation Resistance (V = 500 V)(4)		R_{ISO}	10^{11}	—	—	Ω
Isolation Capacitance (V = 0 V, f = 1 MHz)(4)		C_{ISO}	—	0.2	2	pF

1. Always design to the specified minimum/maximum electrical limits (where applicable).
2. Current Transfer Ratio (CTR) = I_C/I_F x 100%.
3. For test circuit setup and waveforms, refer to Figure 11.
4. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

TYPICAL CHARACTERISTICS

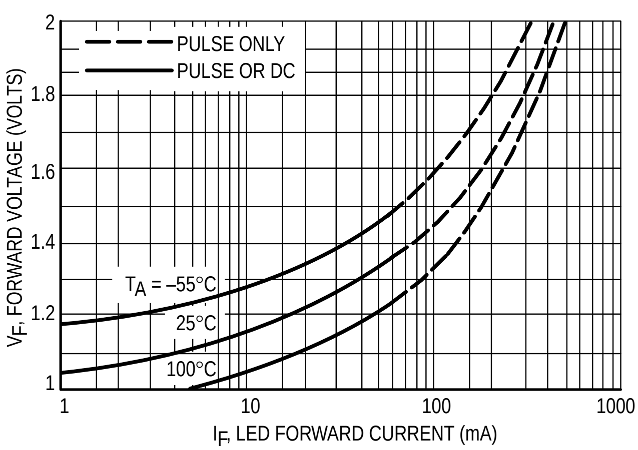


Figure 1. LED Forward Voltage versus Forward Current

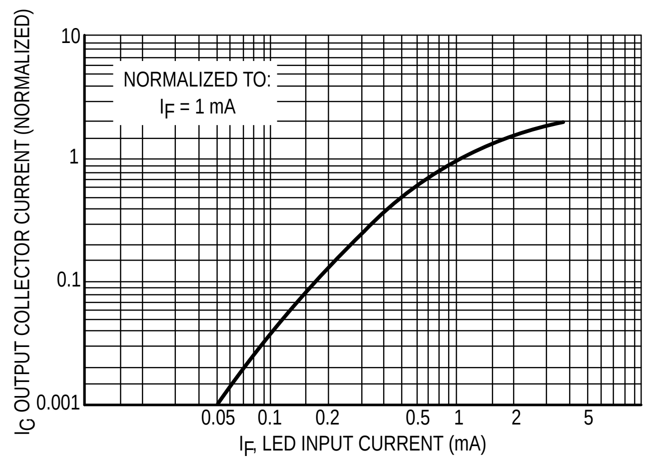


Figure 2. Output Current versus Input Current

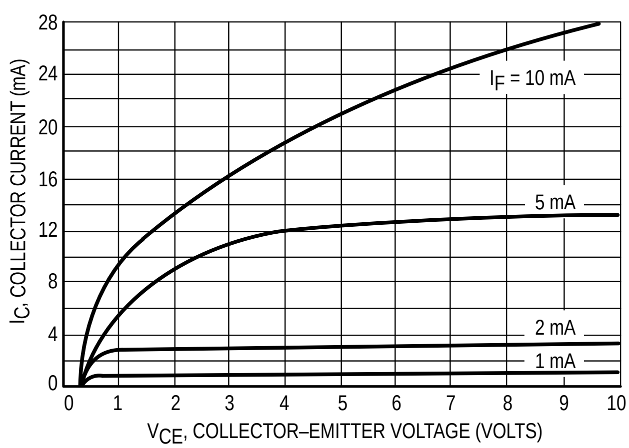


Figure 3. Collector Current versus Collector–Emitter Voltage

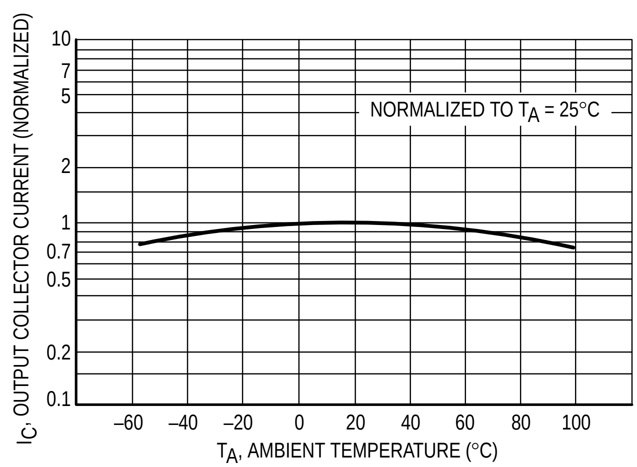


Figure 4. Output Current versus Ambient Temperature

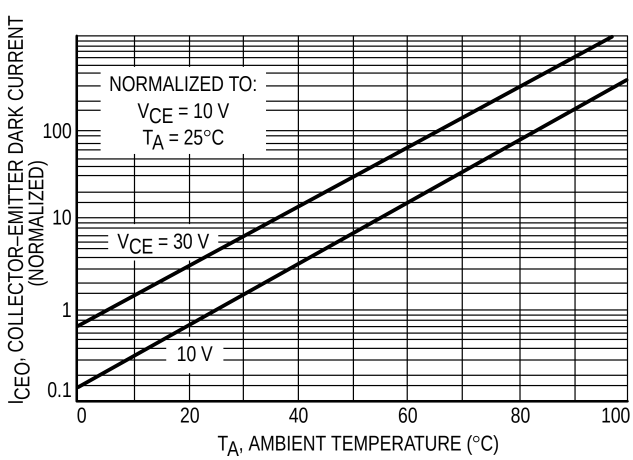


Figure 5. Dark Current versus Ambient Temperature

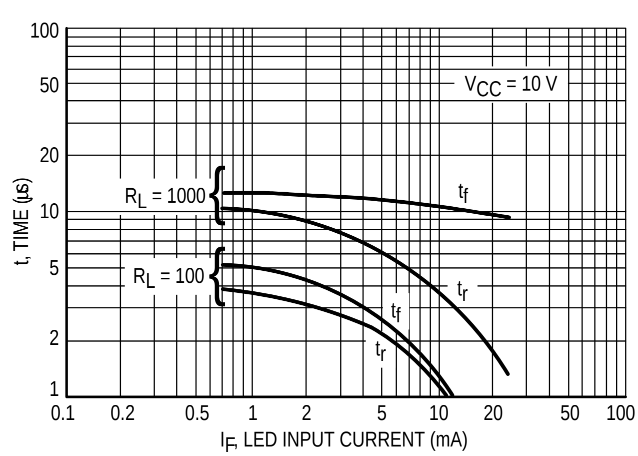


Figure 6. Rise and Fall Times (Typical Values)

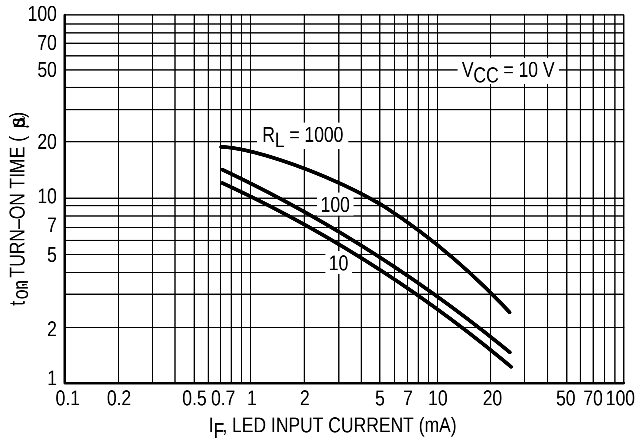


Figure 7. Turn–On Switching Times

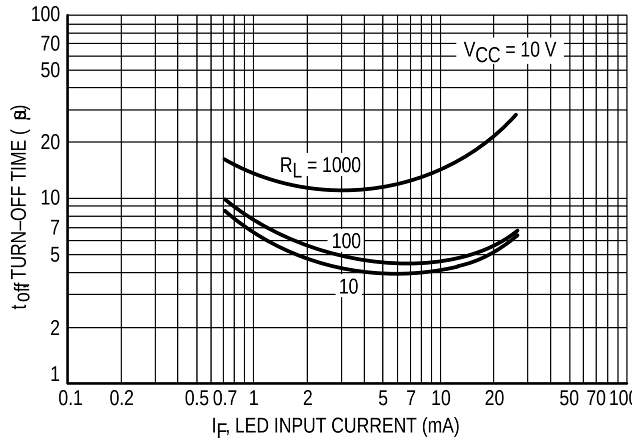


Figure 8. Turn–Off Switching Times

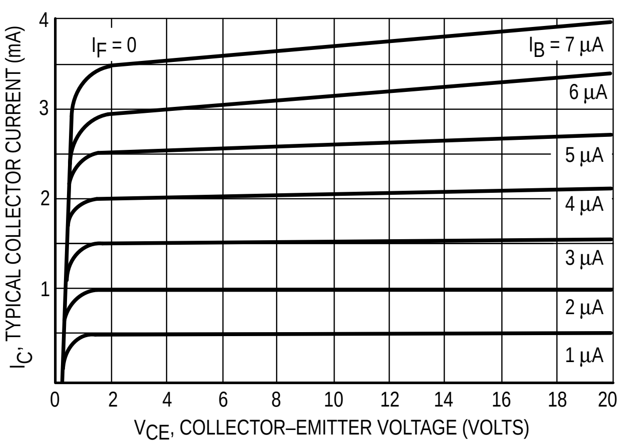


Figure 9. DC Current Gain (Detector Only)

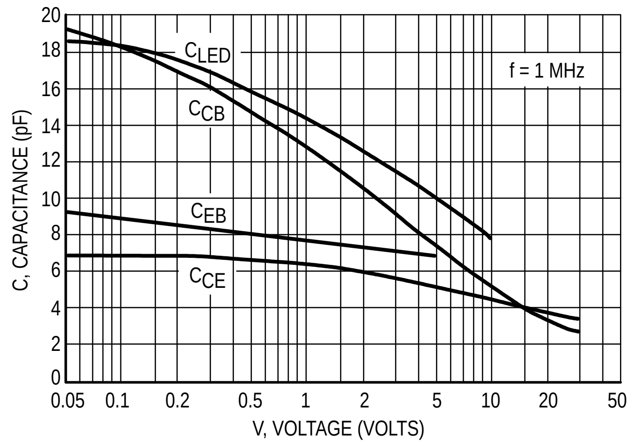


Figure 10. Capacitances versus Voltage

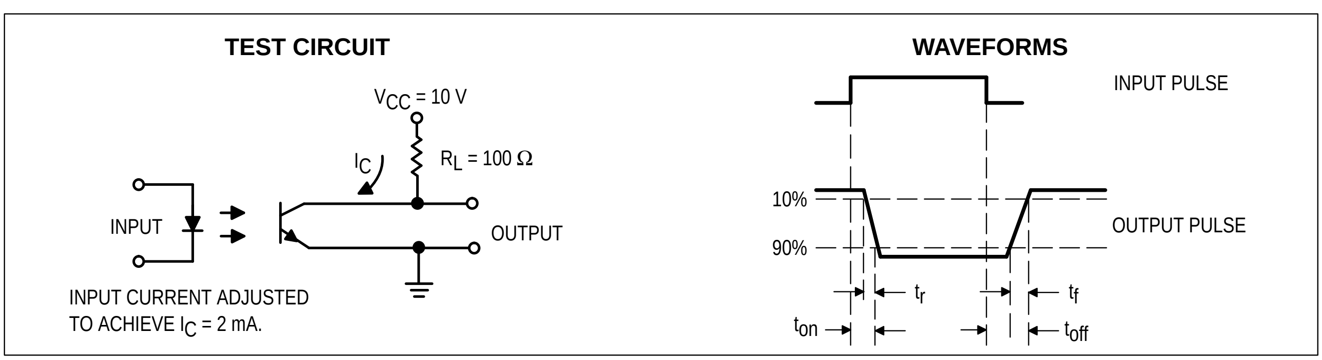
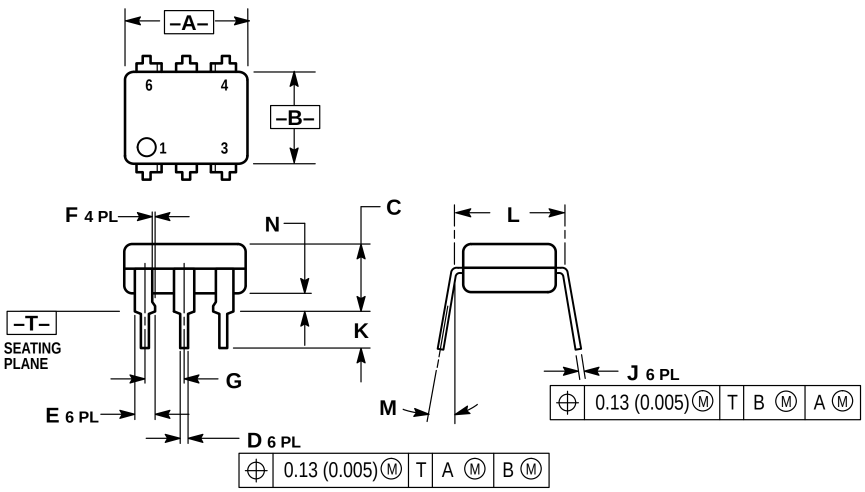


Figure 11. Switching Time Test Circuit and Waveforms

FAIRCHILD SEMICONDUCTOR™

MOC8100

PACKAGE DIMENSIONS

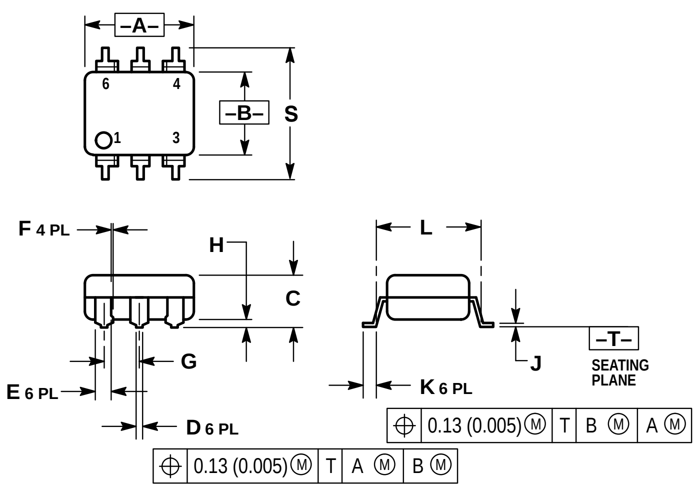


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.320	0.350	8.13	8.89
B	0.240	0.260	6.10	6.60
C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.300 BSC		7.62 BSC	
M	0 °	15 °	0 °	15 °
N	0.015	0.100	0.38	2.54

STYLE 1:
PIN 1. ANODE
2. CATHODE
3. NC
4. EMITTER
5. COLLECTOR
6. BASE

THRU HOLE



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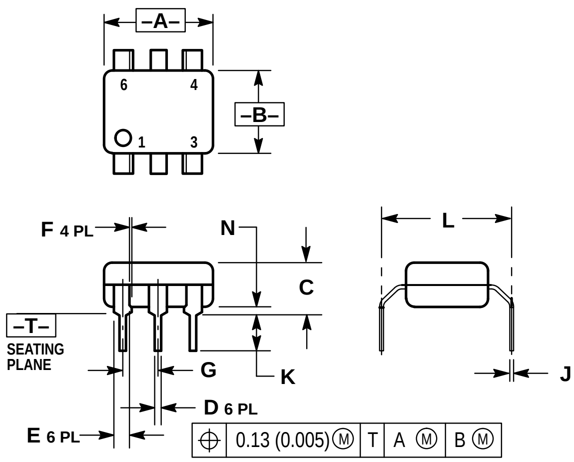
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
H	0.020	0.025	0.51	0.63
J	0.008	0.012	0.20	0.30
K	0.006	0.035	0.16	0.88
L	0.320 BSC		8.13 BSC	
S	0.332	0.390	8.43	9.90

SURFACE MOUNT



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C	0.115	0.200	2.93	5.08
D	0.016	0.020	0.41	0.50
E	0.040	0.070	1.02	1.77
F	0.010	0.014	0.25	0.36
G	0.100 BSC		2.54 BSC	
J	0.008	0.012	0.21	0.30
K	0.100	0.150	2.54	3.81
L	0.400	0.425	10.16	10.80
N	0.015	0.040	0.38	1.02

0.4" LEAD SPACING

DISCLAIMER

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.